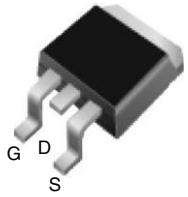
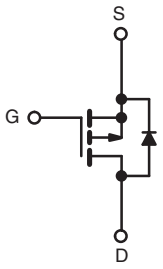
Power MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	- 200	
$R_{DS(on)}$ (Ω)	V_{GS} = - 10 V	3.0
Q_g (Max.) (nC)	11	
Q_{gs} (nC)	7.0	
Q_{gd} (nC)	4.0	
Configuration	Single	

D²PAK (TO-263)





P-Channel MOSFET

FEATURES

- Surface Mount
- Available in Tape and Reel
- Dynamic dV/dt Rating
- P-Channel
- Fast Switching
- Ease of Paralleling
- Simple Drive Requirements
- Lead (Pb)-free Available

Available
RoHS* COMPLIANT

DESCRIPTION

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The D²PAK (TO-263) is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The D²PAK (TO-263) is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0 W in a typical surface mount application.

ORDERING INFORMATION	
Package	D²PAK (TO-263)
Lead (Pb)-free	IRF9610SPbF
	SiHF9610S-E3
SnPb	IRF9610S
	SiHF9610S

ABSOLUTE MAXIMUM RATINGS T_C = 25 °C, unless otherwise noted

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-Source Voltage			V_{DS}	- 200	V
Gate-Source Voltage			V_{GS}	± 20	
Continuous Drain Current	V_{GS} at - 10 V	T_C = 25 °C	I_D	- 1.8	A
		T_C = 100 °C		- 1.0	
Pulsed Drain Current[a]			I_{DM}	- 7.0	
Linear Derating Factor				0.16	W/°C
Linear Derating Factor (PCB Mount)[d]				0.025	
Maximum Power Dissipation	T_C = 25 °C		P_D	20	W
Maximum Power Dissipation (PCB Mount)[d]	T_A = 25 °C			3.0	
Peak Diode Recovery dV/dt[b]			dV/dt	- 5.0	V/ns
Operating Junction and Storage Temperature Range			T_J, T_{stg}	- 55 to + 150	°C
Soldering Recommendations (Peak Temperature)	for 10 s			300[c]	

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).
b. $I_{SD} \leq$ - 1.8 A, dI/dt ≤ 70 A/µs, $V_{DD} \leq V_{DS}$, $T_J \leq$ 150 °C.
c. 1.6 mm from case.
d. When mounted on 1" square PCB (FR-4 or G-10 material).

* Pb containing terminations are not RoHS compliant, exemptions may apply

THERMAL RESISTANCE RATINGS				
PARAMETER	**SYMBOL**	**TYP.**	**MAX.**	**UNIT**
Maximum Junction-to-Ambient	R_{thJA}	-	62	°C/W
Maximum Junction-to-Ambient (PCB Mount)[a]	R_{thJA}	-	40	
Maximum Junction-to-Case (Drain)	R_{thJC}	-	6.4	

Note

a. When mounted on 1" square PCB (FR-4 or G-10 material).

SPECIFICATIONS T_J = 25 °C, unless otherwise noted						
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**MIN.**	**TYP.**	**MAX.**	**UNIT**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 200	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to 25 °C, I_D = - 1 mA	-	- 0.23	-	V/°C
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 2.0	-	- 4.0	V
Gate-Source Leakage	I_{GSS}	V_{GS} = ± 20 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 200 V, V_{GS} = 0 V	-	-	- 100	µA
		V_{DS} = - 160 V, V_{GS} = 0 V, T_J = 125 °C	-	-	- 500	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS} = - 10 V, I_D = - 0.90 A[b]	-	-	3.0	Ω
Forward Transconductance	g_{fs}	V_{DS} = - 50 V, I_D = - 0.90 A[b]	0.90	-	-	S
Dynamic						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = - 25 V, f = 1.0 MHz, see fig. 10	-	170	-	pF
Output Capacitance	C_{oss}		-	50	-	
Reverse Transfer Capacitance	C_{rss}		-	15	-	
Total Gate Charge	Q_g	V_{GS} = - 10 V, I_D = - 3.5 A, V_{DS} = - 160 V, see fig. 11 and 18[b]	-	-	11	nC
Gate-Source Charge	Q_{gs}		-	-	7.0	
Gate-Drain Charge	Q_{gd}		-	-	4.0	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 100 V, I_D = - 0.90 A, R_G = 50 Ω, R_D = 110 Ω, see fig. 17[b]	-	8.0	-	ns
Rise Time	t_r		-	15	-	
Turn-Off Delay Time	$t_{d(off)}$		-	1.0	-	
Fall Time	t_f		-	8.0	-	
Internal Drain Inductance	L_D	Between lead, 6 mm (0.25") from package and center of die contact 	-	4.5	-	nH
Internal Source Inductance	L_S		-	7.5	-	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	- 1.8	A
Pulsed Diode Forward Current[a]	I_{SM}		-	-	- 7.0	
Body Diode Voltage	V_{SD}	T_J = 25 °C, I_S = - 1.8 A, V_{GS} = 0 V[b]	-	-	- 5.8	V
Body Diode Reverse Recovery Time	t_{rr}	T_J = 25 °C, I_F = - 1.8 A, dI/dt = 100 A/µs[b]	-	240	360	ns
Body Diode Reverse Recovery Charge	Q_{rr}		-	1.7	2.6	µC
Forward Turn-On Time	t_{on}	Intrinsic turn-on time is negligible (turn-on is dominated by L_S and L_D)				

Notes

a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 5).

b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

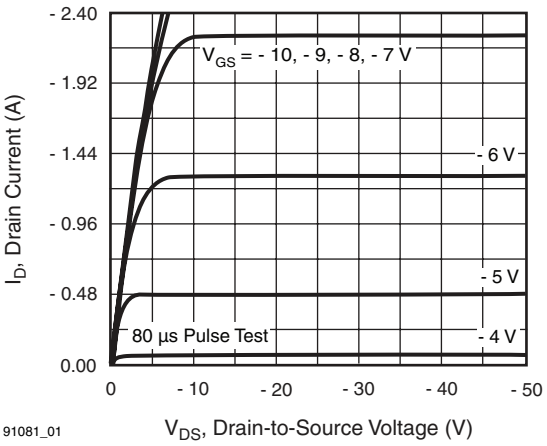


Fig. 1 - Typical Output Characteristics

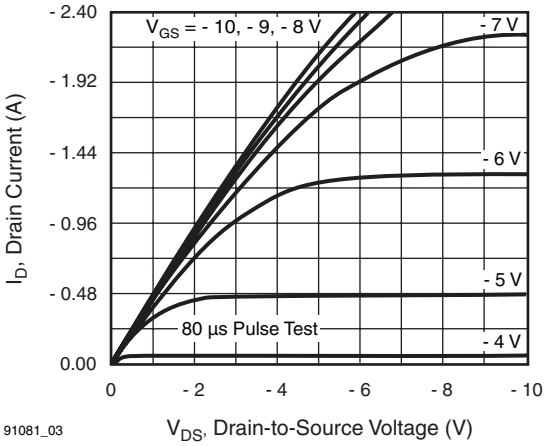


Fig. 3 - Typical Saturation Characteristics

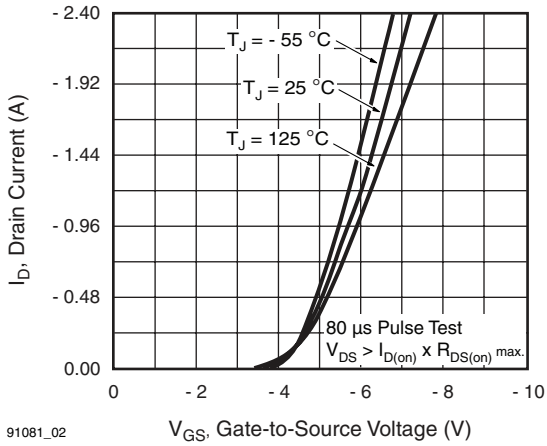


Fig. 2 - Typical Transfer Characteristics

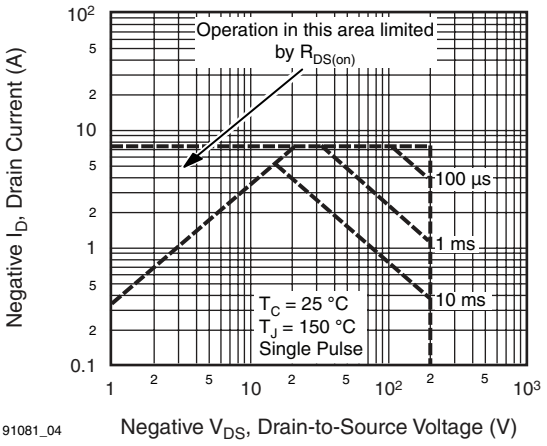


Fig. 4 - Maximum Safe Operating Area

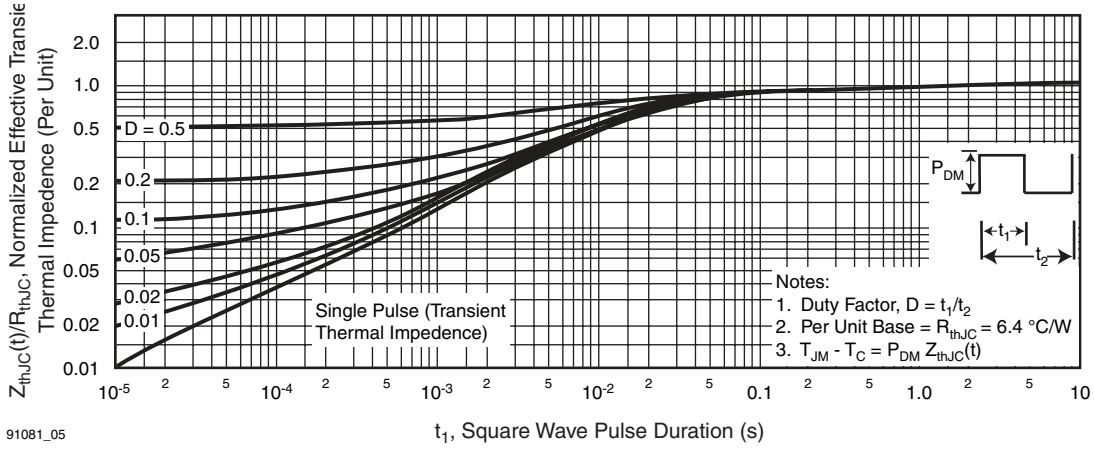


Fig. 5 - Maximum Effective Transient Thermal Impedance, Junction-to.Case vs. Pulse Duration

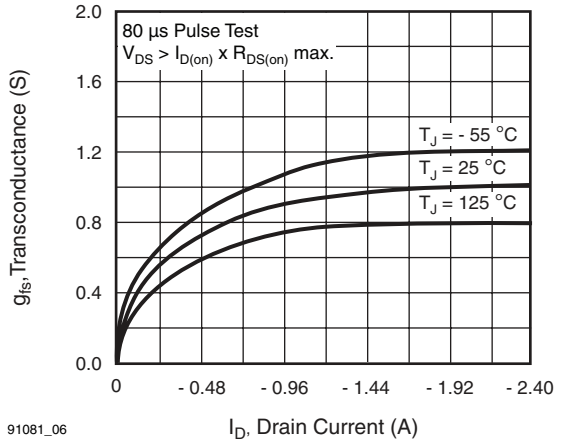


Fig. 6 - Typical Transconductance vs. Drain Current

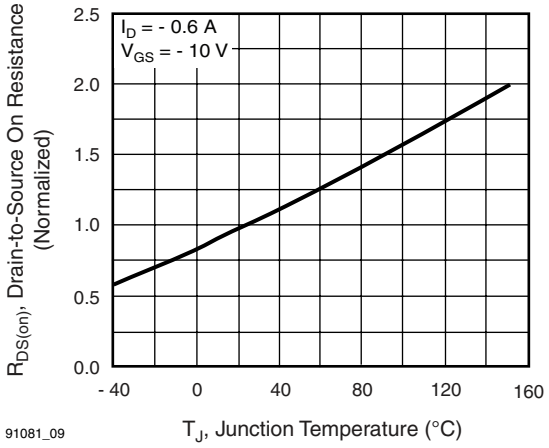


Fig. 9 - Normalized On-Resistance vs. Temperature

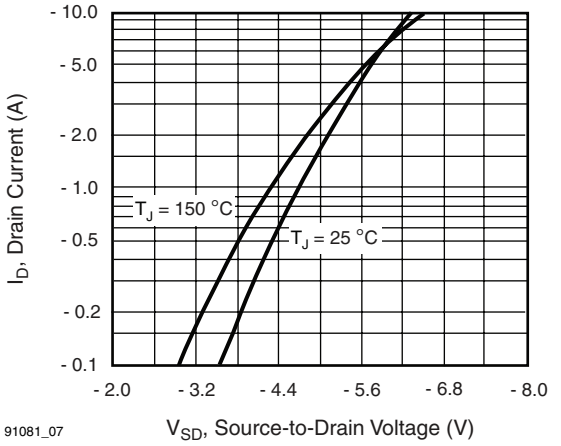


Fig. 7 - Typical Source-Drain Diode Forward Voltage

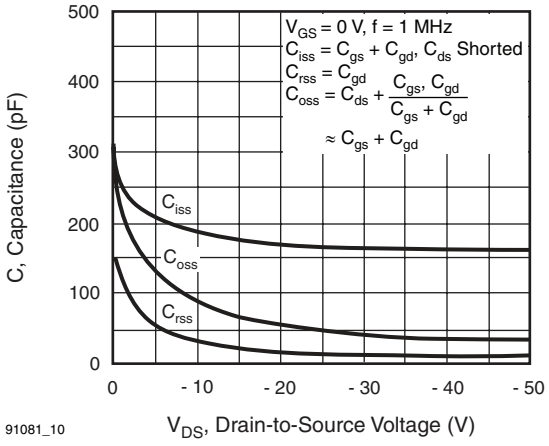


Fig. 10 - Typical Capacitance vs. Drain-to-Source Voltage

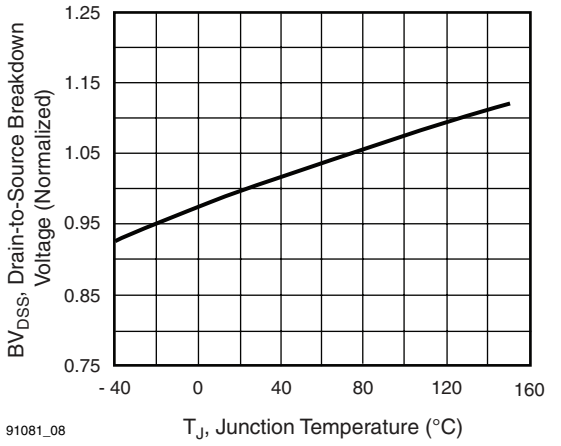


Fig. 8 - Breakdown Voltage vs. Temperature

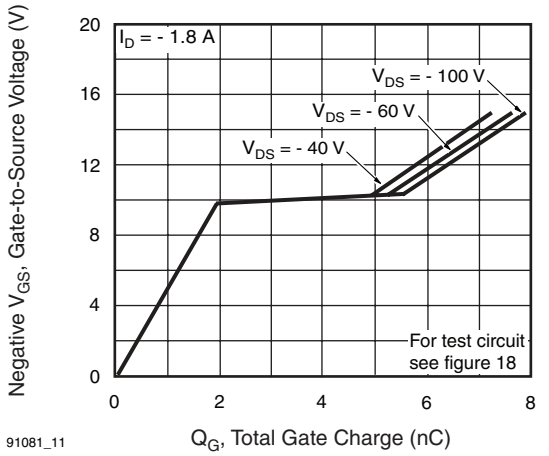


Fig. 11 - Typical Gate Charge vs. Gate-to-Source Voltage

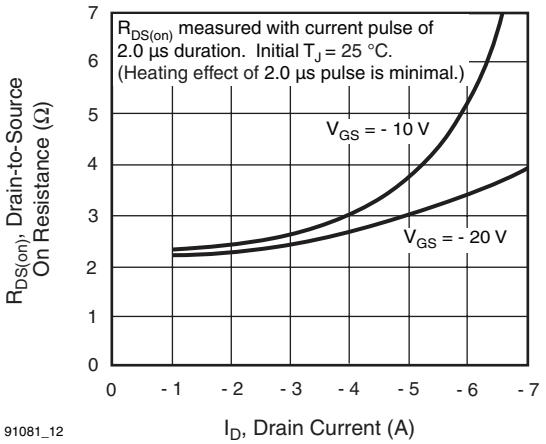


Fig. 12 - Typical On-Resistance vs. Drain Current

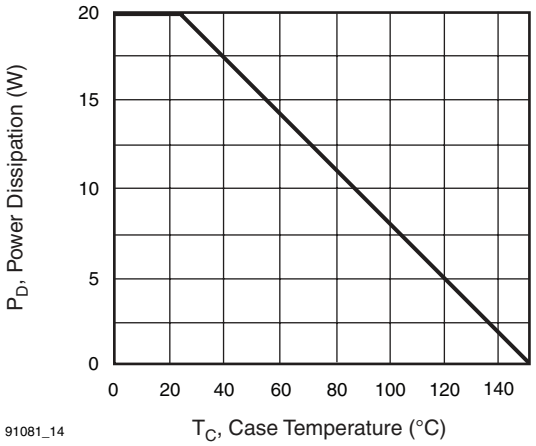


Fig. 14 - Power vs. Temperature Derating Curve

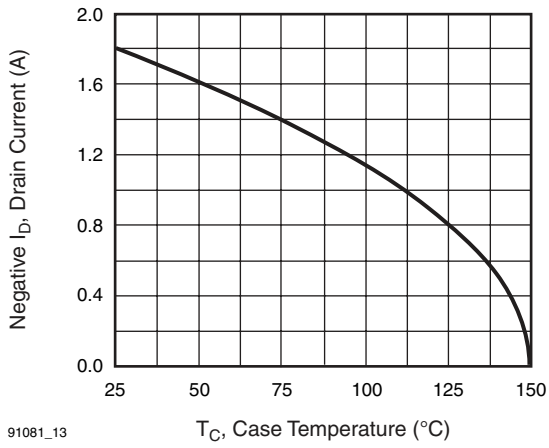


Fig. 13 - Maximum Drain Current vs. Case Temperature

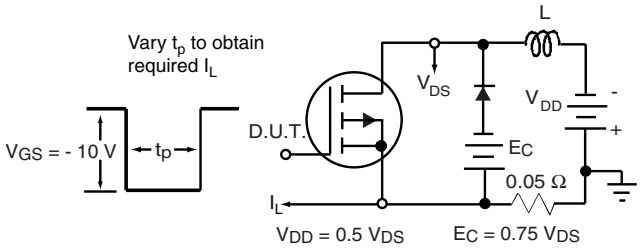


Fig. 15 - Clamped Inductive Test Circuit

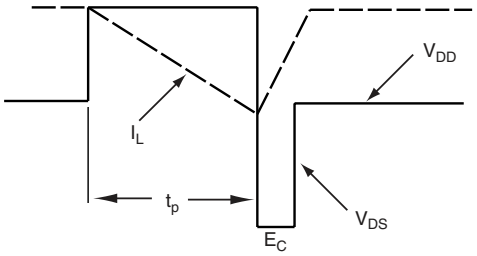


Fig. 16 - Clamped Inductive Waveforms

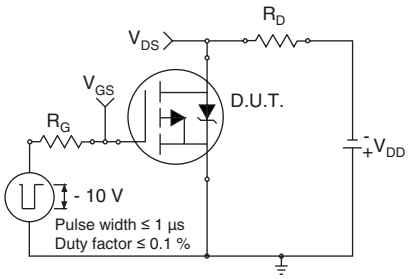


Fig. 17a - Switching Time Test Circuit

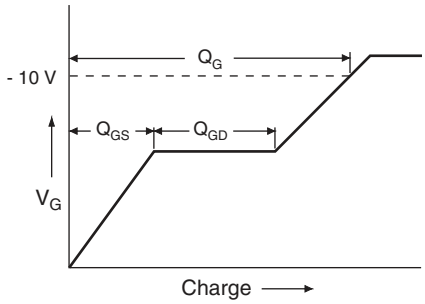


Fig. 18a - Basic Gate Charge Waveform

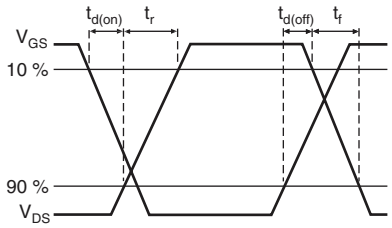


Fig. 17b - Switching Time Waveforms

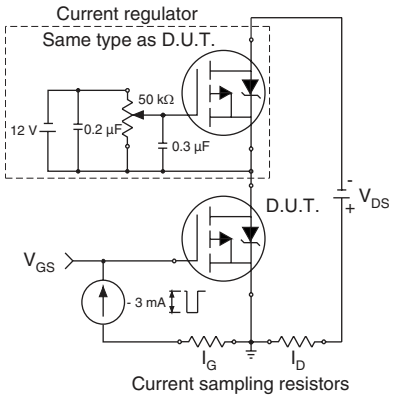
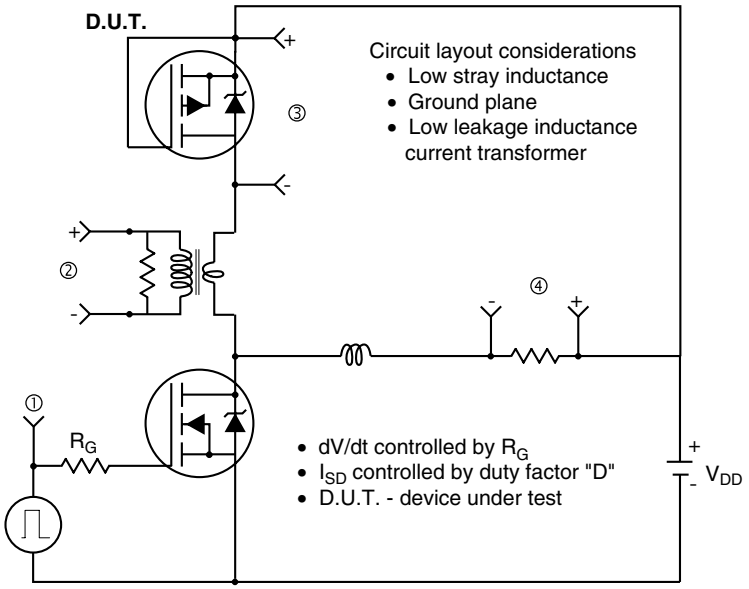
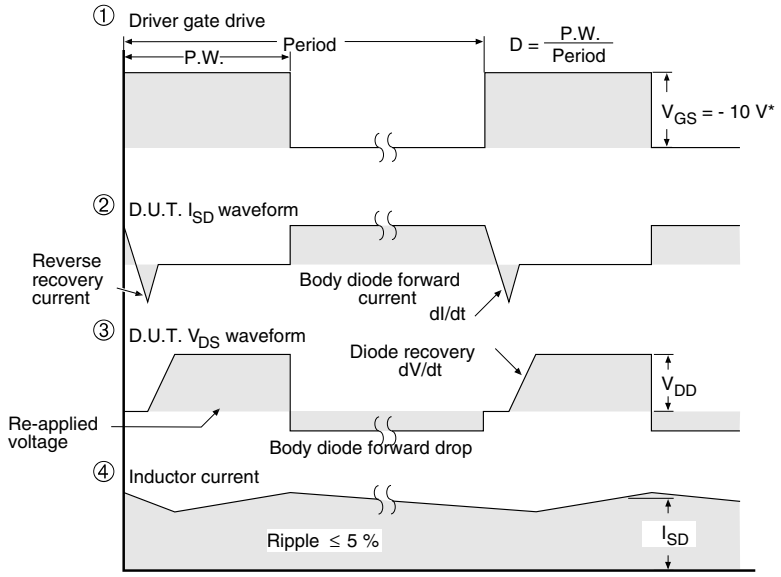


Fig. 18b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



• Compliment N-Channel of D.U.T. for driver



* V_{GS} = - 5 V for logic level and - 3 V drive devices

Fig. 19 - For P-Channel

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